# **M74LS10P**

## TRIPLE 3-INPUT POSITIVE NAND GATES

#### DESCRIPTION

The M74LS10P is a semiconductor integrated circuit containing three triple-input positive NAND and negative NOR gates.

#### **FEATURES**

- High breakdown input voltage (V<sub>I</sub> ≥ 15V)
- Low power dissipation (Pd = 8mW typical)
- High speed (tpd = 6ns typical)
- Low output impedance
- Wide operating temperature range (T<sub>a</sub> = -20 ~ +75°C)

#### **APPLICATION**

General purpose, for use in industrial and consumer equipment.

# **FUNCTIONAL DESCRIPTION**

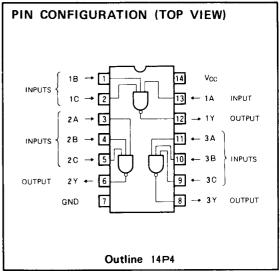
The use Schottky TTL technology has enabled the achievement of high input voltage, high speed, low power dissipation and high fan-out.

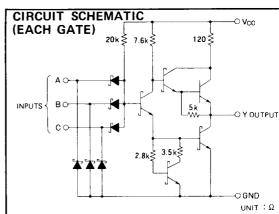
When all inputs A, B and C are high, output Y is low, and when one or more of the inputs is low, Y is high.

# **FUNCTION TABLE**

Α	N	Y
L	L	Ι
н	L	н
L	н	н
Н	н	L

 $N\!=\!B\!\cdot\!C$ 





### ABSOLUTE MAXIMUM RATINGS ( $T_a = -20 \sim +75^{\circ}C$ , unless otherwise noted)

Symbol	Parameter	Conditions	Limits	Unit	
Vcc	Supply voltage		-0.5~+7	V	
VI	Input voltage		-0.5~+15	V	
Vo	Output voltage	High-level state	-0.5~+V <sub>CC</sub>	V	
Topr	Operating free-air ambient temperature range		-20~+75	°C	
Tstg	Storage temperature range		-65~+150	*C	

# TRIPLE 3-INPUT POSITIVE NAND GATES

# **RECOMMENDED OPERATING CONDITIONS** ( $T_a = -20 - +75^{\circ}C$ , unless otherwise noted)

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Symbol	Parame	Parameter		Тур	Max	Unit	
Vcc	Supply voltage		4.75	5	5.25	V	
loH	High-level output current	V <sub>0H</sub> ≥2.7V	0		- 400	μА	
loL	Low-level output current	V <sub>OL</sub> ≦0.4V	0		4	mΑ	
		V <sub>OL</sub> ≤0.5V	0		8	mA	

# **ELECTRICAL CHARACTERISTICS** ( $T_a = -20 \sim \pm 75^{\circ}C$ , unless otherwise noted)

Symbol	Parameter	Test conditions		Limits			
				Min	Тур*	Max	Unit
VIH	High-level input voltage			2			٧
VIL	Low-level input voltage					0.8	V
Vic	Input clamp voltage	V <sub>CC</sub> =4.75V, I <sub>IC</sub> =-18mA				-1.5	V
Voн	High-level output voltage	$V_{CC} = 4.75V$ , $V_1 = 0.8V$ , $I_{OH} = -400\mu A$		2.7	3.4		٧
		V <sub>CC</sub> =4.75V	I <sub>OL</sub> = 4 mA		0.25	0.4	
VoL	Low-level output voltage	V <sub>1</sub> = 2V	I <sub>OL</sub> = 8 mA		0.35	0.5	V
		V <sub>CC</sub> =5.25V, V <sub>I</sub> =2	.7Ŷ			20	μΑ
ин .	High-level input current	V <sub>CC</sub> =5.25V, V <sub>I</sub> =1	0V			0.1	mA
liL	Low-level input current	V <sub>CC</sub> =5.25V, V <sub>I</sub> =0.4V				-0.4	mA
los	Short-circuit output current (Note 1)	V <sub>CC</sub> =5.25V, V <sub>O</sub> =0V		<b>- 20</b>		100	mA
Icch	Supply current, all outputs high	V <sub>CC</sub> =5.25V, V <sub>I</sub> =0V			0.6	1.2	mA
I <sub>CCL</sub>	Supply current, all outputs low	V <sub>CC</sub> =5.25V, V <sub>I</sub> =4.5V			1.8	3.3	mA

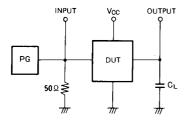
<sup>\* :</sup> All typical values are at V<sub>CC</sub> = 5V, Ta = 25°C.

Note 1: All measurements should be done quickly, and not more than one output should be shorted at a time.

## **SWITCHING CHARACTERISTICS** (V<sub>CC</sub>=5V, Ta=25°C, unless otherwise noted)

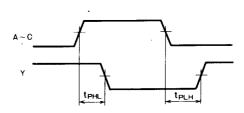
Combat		Test conditions	Limits			Unit
Symbol	Parameter		Min	Тур	Max	Unit
tpLH	Low-to-high-level output propagation time	C <sub>L</sub> = 15pF		6	15	ns
t <sub>PHL</sub>	High-to-low-level output propagation time	(Note 2)		9	15	ns

Note 2: Measurement circuit



- (1) The pulse generator (PG) has the following characteristics: PRR = 1MHz,  $t_f$  = 6ns,  $t_f$  = 6ns,  $t_w$  = 500ns,  $V_P$  = 3 $V_{P,P}$ ,  $Z_O$  = 50 $\Omega$
- (2) C<sub>L</sub> includes probe and jig capacitance.

# TIMING DIAGRAM (Reference level = 1.3V)



# MITSUBISHI LSTTLs **PACKAGE OUTLINES**

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